

IGBT Module

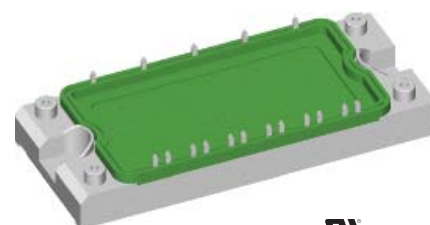
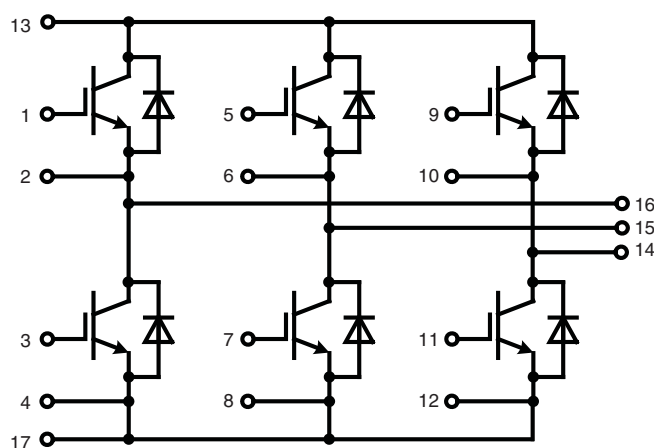
Sixpack

Short Circuit SOA Capability
Square RBSOA

$$\begin{aligned} I_{C25} &= 30 \text{ A} \\ V_{CES} &= 1200 \text{ V} \\ V_{CE(sat) \text{ typ.}} &= 2.0 \text{ V} \end{aligned}$$

Part name (Marking on product)

MWI15-12A7



 E72873

Pin configuration see outlines.

Features:

- NPT IGBT technology
- low saturation voltage
- positive temperature coefficient for easy paralleling
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- space savings
- reduced protection circuits

Application:

- AC motor control
- AC servo and robot drives
- power supplies

Package:

- UL registered
- Industry standard E2-pack
- package with copper base plate
- package designed for wave soldering

IGBTs

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			1200		V
V_{GES}	max. DC gate voltage	continuous			± 20		V
V_{GEM}	max. transient collector gate voltage	transient			± 30		V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			30		A
I_{C80}		$T_C = 80^{\circ}\text{C}$			20		A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			140		W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15\text{ A}; V_{GE} = 15\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.0 2.3	2.6	V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.6\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	4.5		6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.8	0.9	mA mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$				200	nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$			1000		pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 15\text{ A}$			70		nC
$t_{d(on)}$	turn-on delay time	} inductive load $V_{CE} = 600\text{ V}; I_C = 15\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$		100		ns
t_r	current rise time				75		ns
$t_{d(off)}$	turn-off delay time				500		ns
t_f	current fall time				70		ns
E_{on}	turn-on energy per pulse				2.3		mJ
E_{off}	turn-off energy per pulse				1.8		mJ
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$ $L = 100\ \mu\text{H}$; clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$		35		A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = V_{CES}; V_{GE} = \pm 15\text{ V};$ $R_G = 82\ \Omega$; non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$		10		μs
R_{thJC}	thermal resistance junction to case	(per IGBT)				0.88	K/W

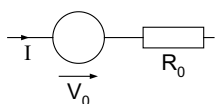
Diodes

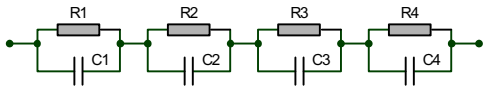
Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 150^{\circ}\text{C}$			1200		V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			25		A
I_{F80}		$T_C = 80^{\circ}\text{C}$			17		A
V_F	forward voltage	$I_F = 15\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.4 1.7	2.7		V V
I_{RM}	max. reverse recovery current	} $V_R = 600\text{ V}$ $di_F/dt = -400\text{ A}/\mu\text{s}$ $I_F = 15\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$		16		A
t_{rr}	reverse recovery time				130		ns
$E_{rec(off)}$	reverse recovery energy				0.49		mJ
R_{thJC}	thermal resistance junction to case	(per diode)				2.1	K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Module
Ratings

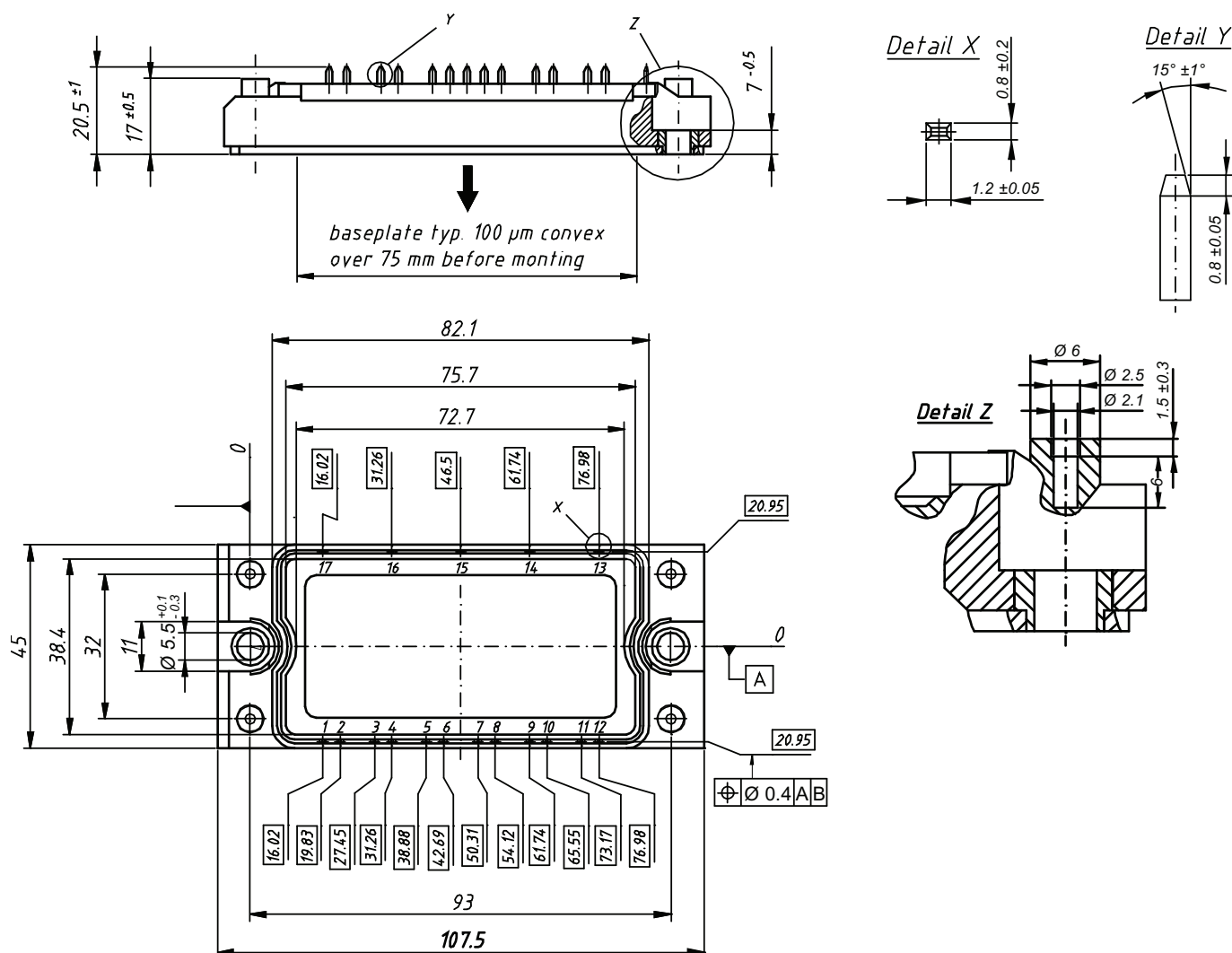
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
T_{VJ}	operating temperature		-40		125	°C
T_{VJM}	max. virtual junction temperature				150	°C
T_{stg}	storage temperature		-40		125	°C
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$			2500	V~
M_d	mounting torque	(M4)	2.7		3.3	Nm
d_s	creep distance on surface		6			mm
d_A	strike distance through air		6			mm
Weight				180		g
R_{thCH}	thermal resistance case to heatsink	with heatsink compound		0.02		K/W

Equivalent Circuits for Simulation

Ratings

Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_0 R_0	IGBT	T1 - T6 $T_{VJ} = 125^\circ\text{C}$		1.37 62		V mΩ
V_0 R_0	Diode	D1 - D6 $T_{VJ} = 125^\circ\text{C}$		1.327 30		V mΩ
 $Z_{th}(t) = \sum_{i=1}^n \left[R_i \cdot \left(1 - \exp\left(-\frac{t}{\tau_i}\right) \right) \right]$ $\tau_i = R_i \cdot C_i$						
				IGBT		
				Diode		
R_1			-		-	
R_2			-		-	
C_1			-		-	
C_2			-		-	

Outline Drawing

Dimensions in mm (1 mm = 0.0394")


Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MWI 15-12A7	MWI15-12A7	Box	10	485063

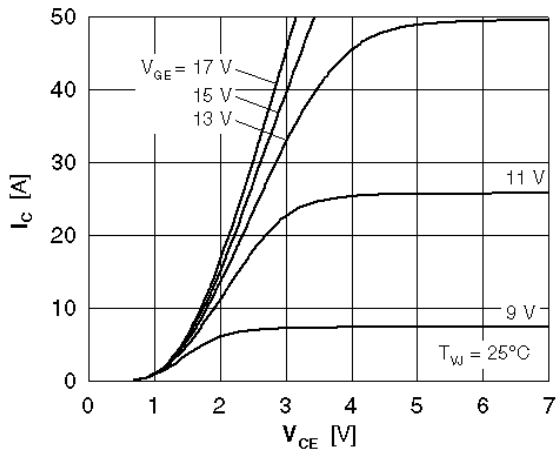


Fig. 1 Typ. output characteristics

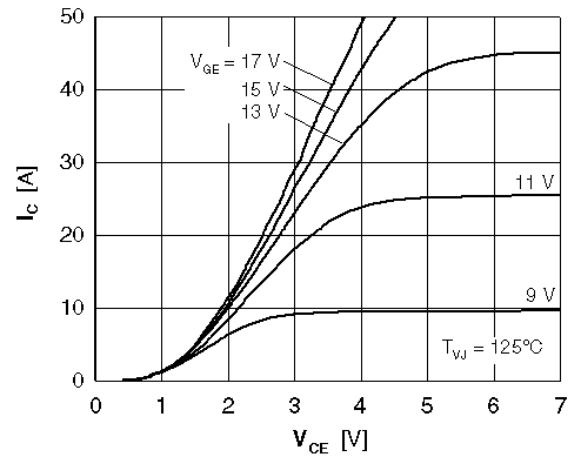


Fig. 2 Typ. output characteristics

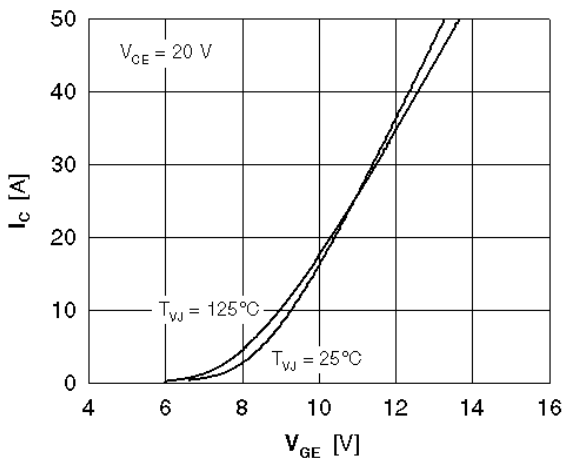


Fig. 3 Typ. transfer characteristics

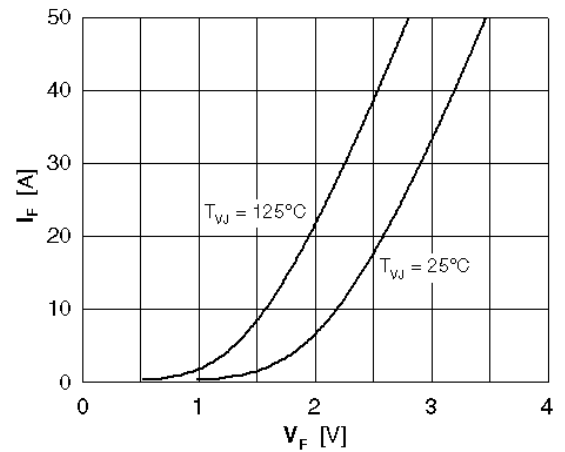


Fig. 4 Typ. forward characteristics of free wheeling diode

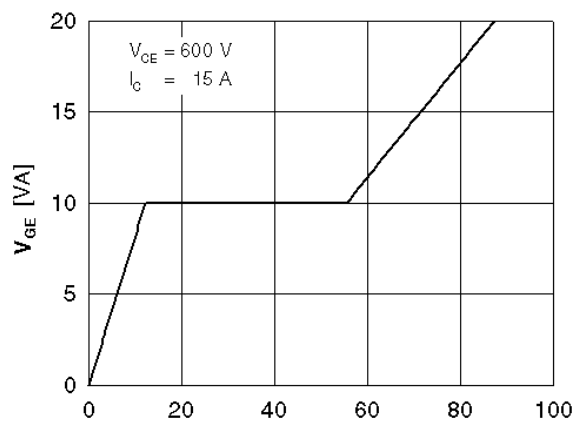


Fig. 5 Typ. turn on gate charge

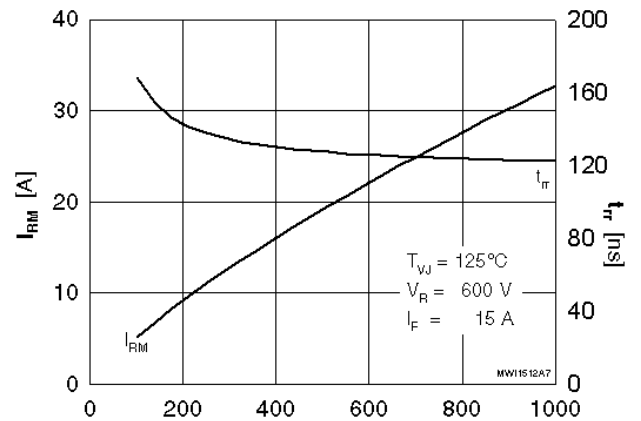


Fig. 6 Typ. turn off characteristics of free wheeling diode

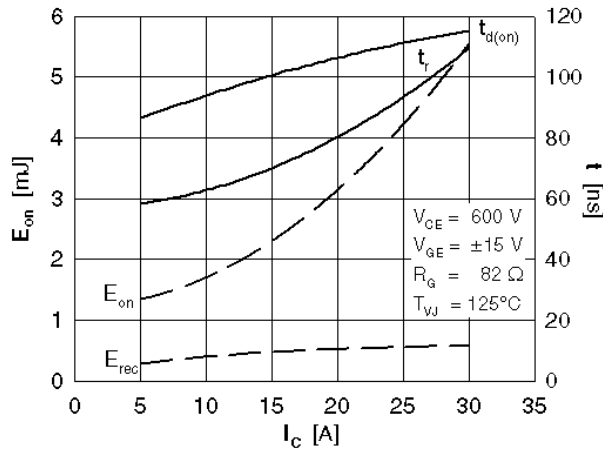


Fig. 7 Typ. turn on energy and switching times versus collector current

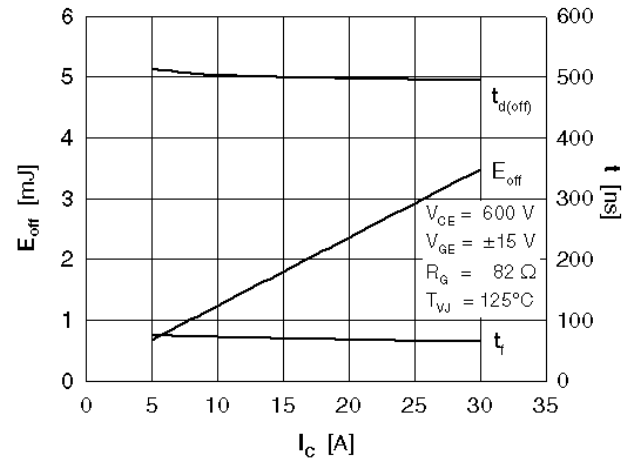


Fig. 8 Typ. turn off energy and switching times versus collector current

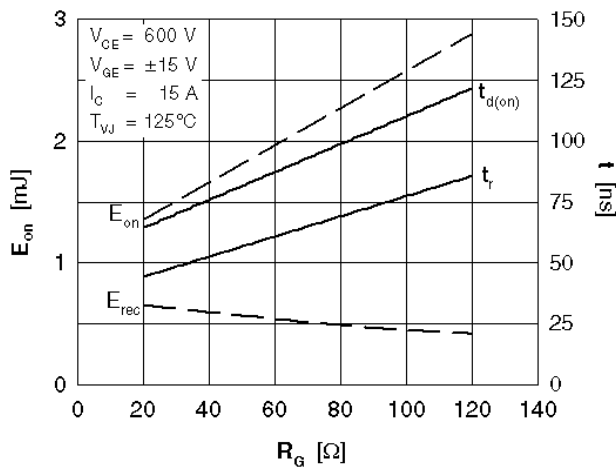


Fig. 9 Typ. turn on energy and switching times versus gate resistor

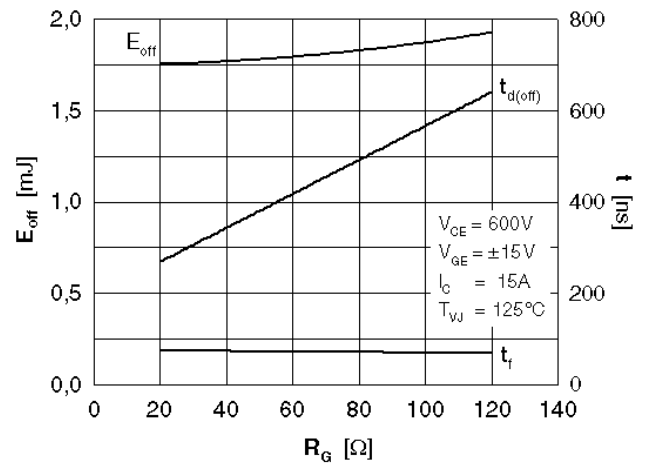


Fig. 10 Typ. turn off energy and switching times versus gate resistor

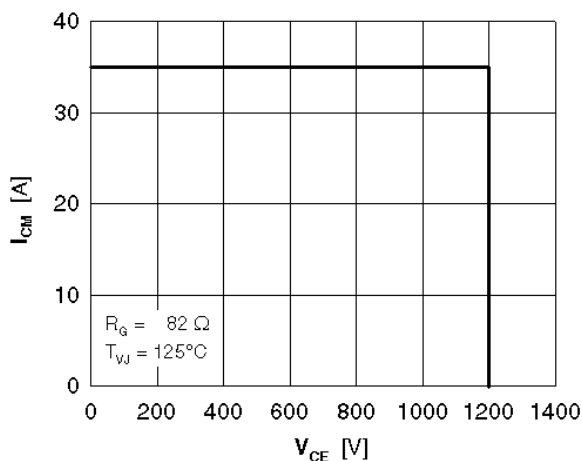


Fig. 11 Reverse biased safe operating area

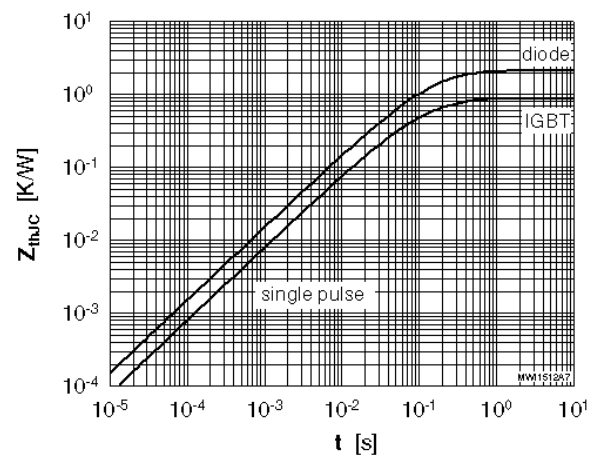


Fig. 12 Typ. transient thermal impedance